

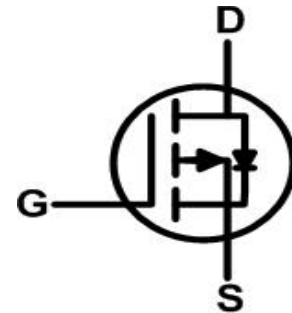


- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

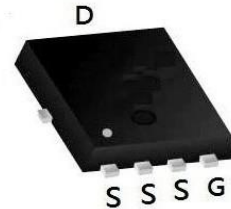
### Description

The WLQ50P03D is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WLQ50P03D meet the RoHS and Gree Product requirement 100% EAS guaranteed with full function reliability approved.



### PDFN3333 Pin Configuration



### Product Summary

| BVDSS | RDSON | ID   |
|-------|-------|------|
| -30V  | 8.7mΩ | -50A |

### Absolute Maximum Ratings

| Symbol                                | Parameter   | Rating     |              | Units |
|---------------------------------------|---|------------|--------------|-------|
|                                       |   | 10s        | Steady State |       |
| V <sub>DS</sub>                       | Drain-Source Voltage  | -30        |              | V     |
| V <sub>GS</sub>                       | Gate-Source Voltage   | ±25        |              | V     |
| I <sub>D</sub> @T <sub>C</sub> =25°C  | Continuous Drain Current, V <sub>GS</sub> @ -10V <sup>1</sup> | -50        |              | A     |
| I <sub>D</sub> @T <sub>C</sub> =100°C | Continuous Drain Current, V <sub>GS</sub> @ -10V <sup>1</sup> | -32        |              | A     |
| I <sub>DM</sub>                       | Pulsed Drain Current <sup>2</sup>                             | -150       |              | A     |
| EAS                                   | Single Pulse Avalanche Energy <sup>3</sup>                    | 125        |              | mJ    |
| I <sub>AS</sub>                       | Avalanche Current   | -50        |              | A     |
| P <sub>D</sub> @T <sub>A</sub> =25°C  | Total Power Dissipation <sup>4</sup>                          | 5          | 2.0          | W     |
| T <sub>STG</sub>                      | Storage Temperature Range                                     | -55 to 150 |              | °C    |
| T <sub>J</sub>                        | Operating Junction Temperature Range                          | -55 to 150 |              | °C    |

### Thermal Data

| Symbol           | Parameter  | Typ. | Max. | Unit |
|------------------|--|------|------|------|
| R <sub>θJA</sub> | Thermal Resistance Junction-Ambient <sup>1</sup> | ---  | 62   | °C/W |



### Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise specified)

| Symbol  | Parameter  | Test Condition  | Min. | Typ. | Max. | Units |
|---|--|---|------|------|------|-------|
| <b>Off Characteristic</b>                                     |  |   |      |      |      |       |
| V <sub>(BR)DSS</sub>  | Drain-Source Breakdown Voltage                           | V <sub>GS</sub> =0V, I <sub>D</sub> = -250μA  | -30  | -    | -    | V     |
| I <sub>DSS</sub>  | Zero Gate Voltage Drain Current                          | V <sub>DS</sub> = -30V, V <sub>GS</sub> =0V,  | -    | -    | -1   | μA    |
| I <sub>GSS</sub>  | Gate to Body Leakage Current                             | V <sub>DS</sub> =0V, V <sub>GS</sub> = ±20V   | -    | -    | ±100 | nA    |
| <b>On Characteristics</b>                                     |  |   |      |      |      |       |
| V <sub>GS(th)</sub>   | Gate Threshold Voltage                                   | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> = -250μA                                      | -1.0 | -1.6 | -2.5 | V     |
| R <sub>DS(on)</sub>   | Static Drain-Source on-Resistance<br>Note3               | V <sub>GS</sub> = -10V, I <sub>D</sub> = -10A   | -    | 8.7  | 14   | mΩ    |
|   |  | V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -5A   | -    | 17   | 24   |       |
| <b>Dynamic Characteristics</b>                                |  |   |      |      |      |       |
| C <sub>iss</sub>  | Input Capacitance  | V <sub>DS</sub> = -15V, V <sub>GS</sub> =0V,<br>f=1.0MHz  | -    | 1770 | -    | pF    |
| C <sub>oss</sub>  | Output Capacitance                                       |   | -    | 233  | -    | pF    |
| C <sub>rss</sub>  | Reverse Transfer Capacitance                             |   | -    | 206  | -    | pF    |
| Q <sub>g</sub>  | Total Gate Charge  | V <sub>DS</sub> = -15V, I <sub>D</sub> = -5A,<br>V <sub>GS</sub> = -10V                         | -    | 22   | -    | nC    |
| Q <sub>gs</sub>   | Gate-Source Charge                                       |   | -    | 1.0  | -    | nC    |
| Q <sub>gd</sub>   | Gate-Drain("Miller") Charge                              |   | -    | 1.8  | -    | nC    |
| <b>Switching Characteristics</b>                              |  |   |      |      |      |       |
| t <sub>d(on)</sub>  | Turn-on Delay Time                                       | V <sub>DD</sub> = -15V, I <sub>D</sub> = -10A,<br>V <sub>GS</sub> =-10V, R <sub>GEN</sub> =2.5Ω | -    | 9    | -    | ns    |
| t <sub>r</sub>  | Turn-on Rise Time  |   | -    | 13   | -    | ns    |
| t <sub>d(off)</sub>   | Turn-off Delay Time                                      |   | -    | 48   | -    | ns    |
| t <sub>f</sub>  | Turn-off Fall Time                                       |   | -    | 20   | -    | ns    |
| <b>Drain-Source Diode Characteristics and Maximum Ratings</b> |  |   |      |      |      |       |
| I <sub>S</sub>  | Maximum Continuous Drain to Source Diode Forward Current |   | -    | -    | -15  | A     |
| I <sub>SM</sub>   | Maximum Pulsed Drain to Source Diode Forward Current     |   | -    | -    | -60  | A     |
| V <sub>SD</sub>   | Drain to Source Diode Forward Voltage                    | V <sub>GS</sub> =0V, I <sub>S</sub> = -15A  | -    | -0.8 | -1.2 | V     |
| t <sub>rr</sub>   | Reverse Recovery Time                                    | T <sub>J</sub> =25°C,   | -    | 64   | -    | ns    |
| Q <sub>rr</sub>   | Reverse Recovery Charge                                  | V <sub>DD</sub> = -24V, I <sub>F</sub> =-2.8A,<br>di/dt=-100A/μs                                | -    | 25   | -    | nC    |

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

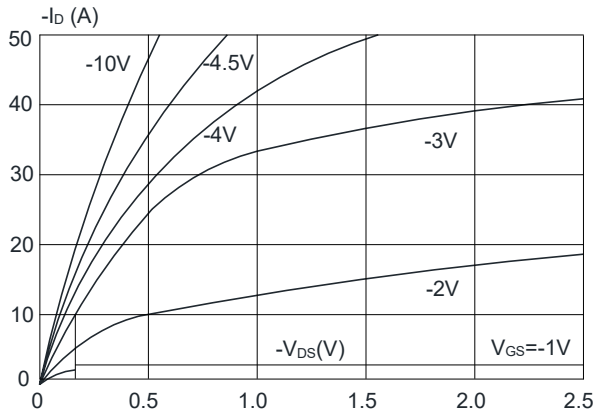
2. EAS condition: T<sub>J</sub>=25°C, V<sub>GS</sub>=10V, R<sub>G</sub>=25Ω, L=0.5mH, I<sub>AS</sub>=-12.7A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

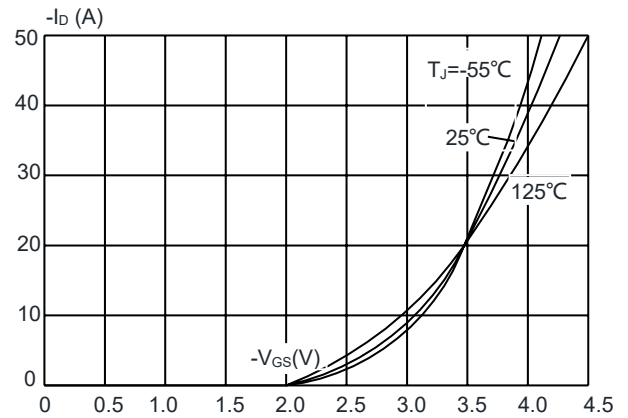


### Typical Performance Characteristics

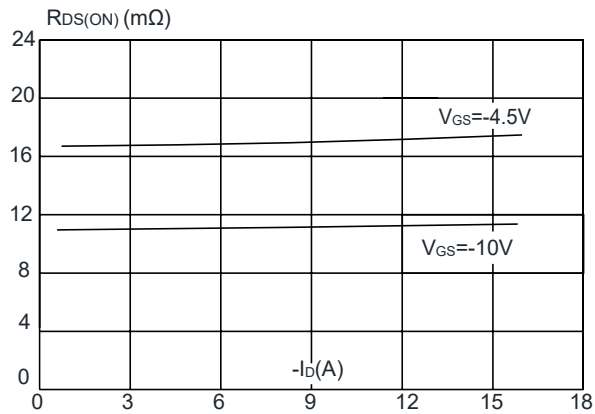
**Figure 1: Output Characteristics**



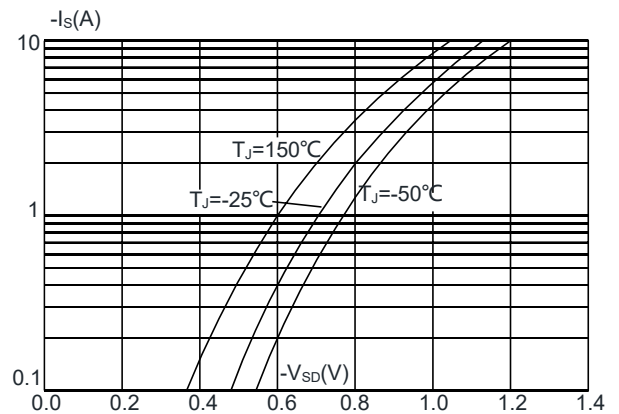
**Figure 2: Typical Transfer Characteristics**



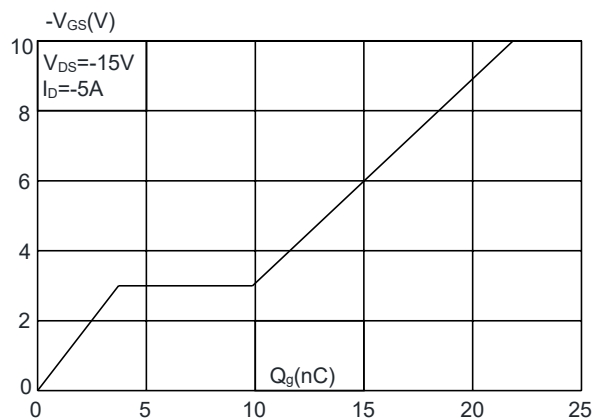
**Figure 3: On-resistance vs. Drain Current**



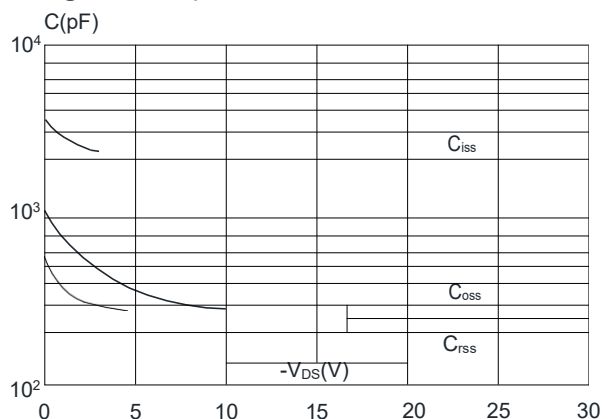
**Figure 4: Body Diode Characteristics**



**Figure 5: Gate Charge Characteristics**

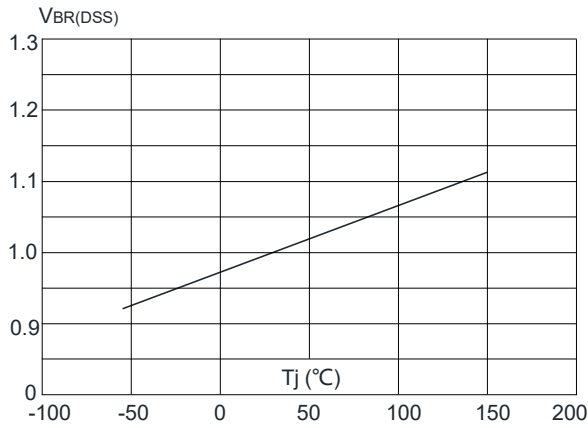


**Figure 6: Capacitance Characteristics**

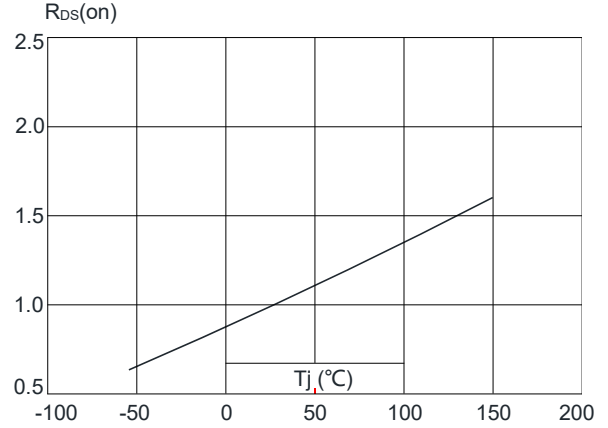




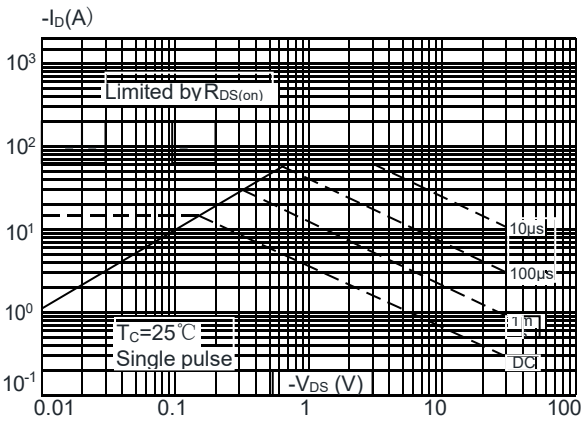
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



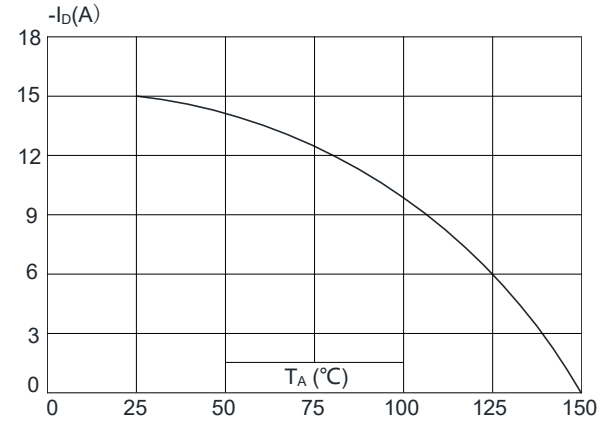
**Figure 8:** Normalized on Resistance vs. Junction Temperature



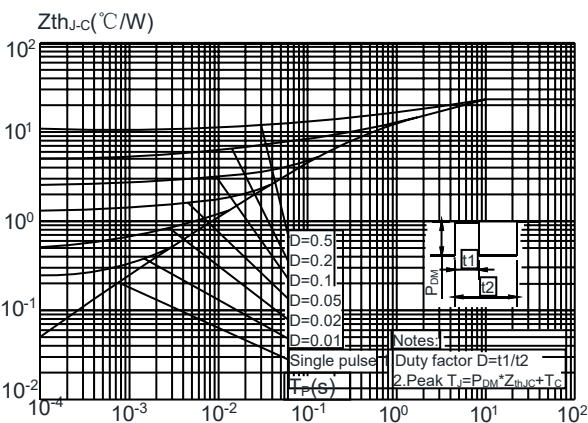
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature



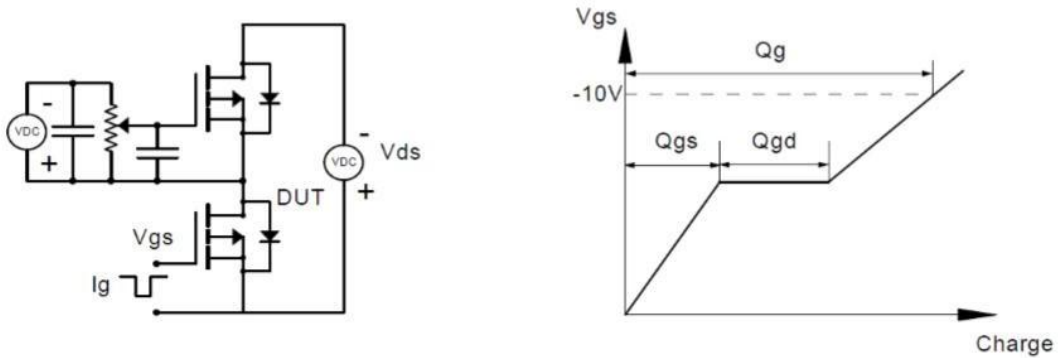
**Figure 11:** Maximum Effective Transient Thermal Impedance, Junction-to-Case



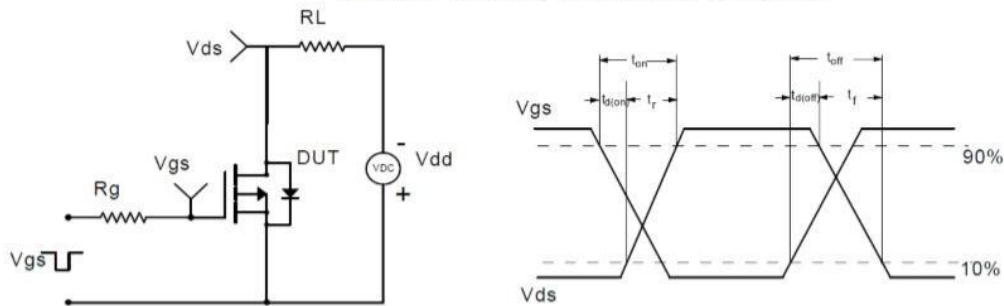


### Test Circuit

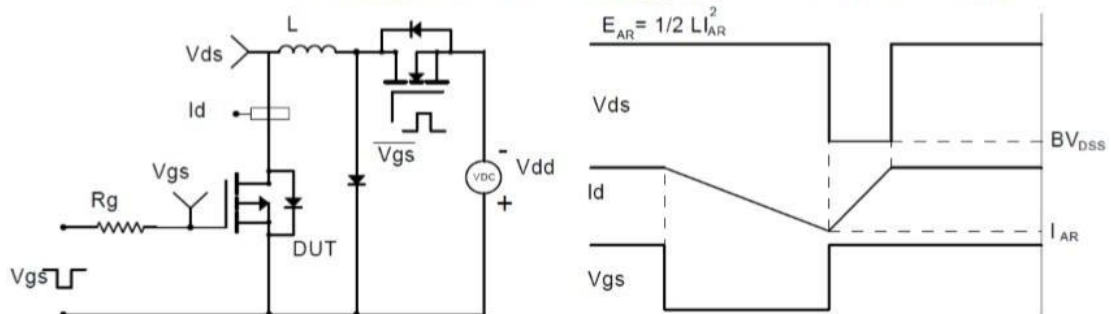
#### Gate Charge Test Circuit & Waveform



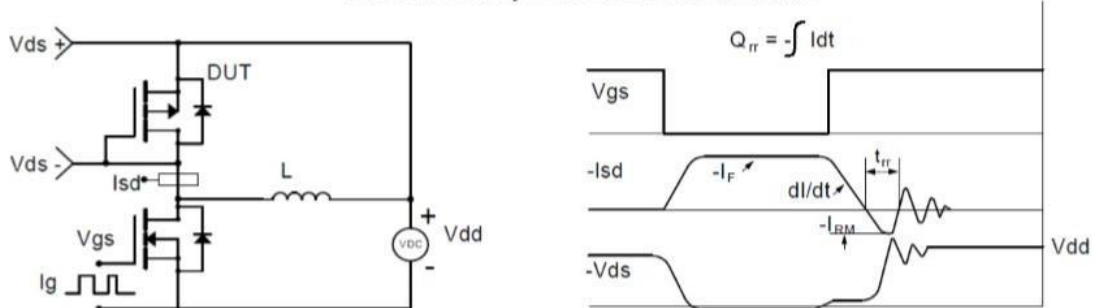
#### Resistive Switching Test Circuit & Waveforms



#### Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

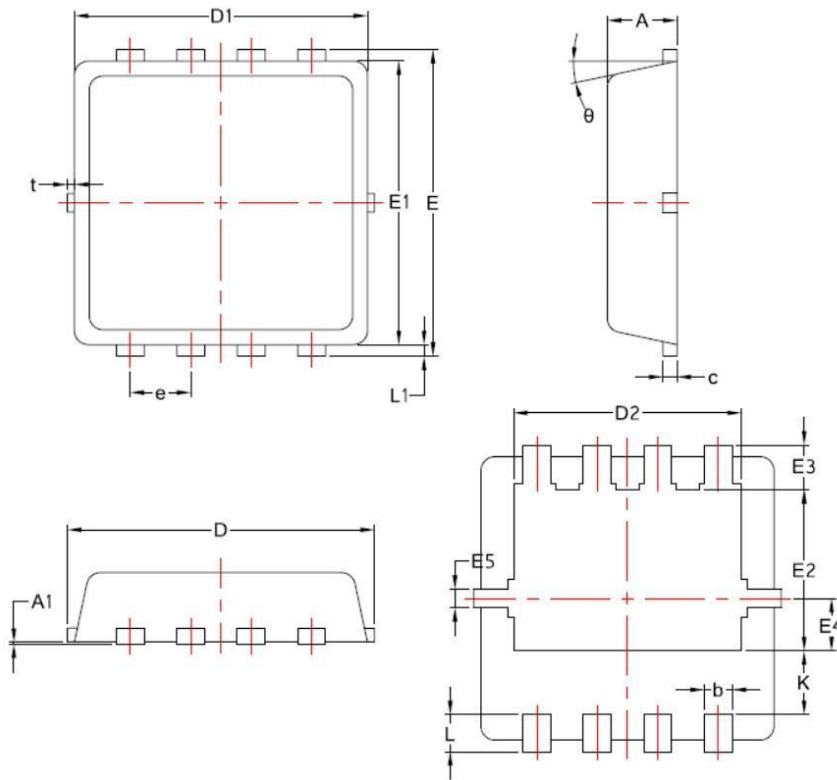


#### Diode Recovery Test Circuit & Waveforms





Package Mechanical Data- PDFN3.3X3.3-8L



| SYMBOL | COMMON |       |      |
|--------|--------|-------|------|
|        | MM     |       |      |
|        | MIN    | NOM   | MAX  |
| A      | 0.70   | 0.75  | 0.85 |
| A1     | /      | /     | 0.05 |
| b      | 0.20   | 0.30  | 0.40 |
| c      | 0.10   | 0.152 | 0.25 |
| D      | 3.15   | 3.30  | 3.45 |
| D1     | 3.00   | 3.15  | 3.25 |
| D2     | 2.29   | 2.45  | 2.65 |
| E      | 3.15   | 3.30  | 3.45 |
| E1     | 2.90   | 3.05  | 3.20 |
| E2     | 1.54   | 1.74  | 1.94 |
| E3     | 0.28   | 0.48  | 0.65 |
| E4     | 0.37   | 0.57  | 0.77 |
| E5     | 0.10   | 0.20  | 0.30 |
| e      | 0.60   | 0.65  | 0.70 |
| K      | 0.59   | 0.69  | 0.89 |
| L      | 0.30   | 0.40  | 0.50 |
| L1     | 0.06   | 0.125 | 0.20 |
| t      | 0      | 0.075 | 0.13 |
| θ      | 10°    | 12°   | 14°  |



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